HFZT

KTC3876

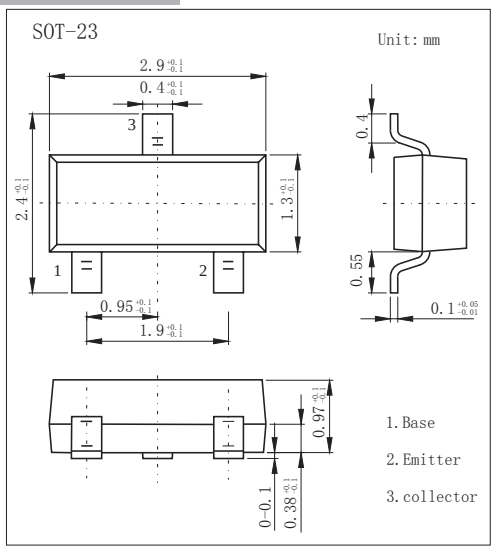
SOT-23 Plastic-Encapsulate Transistors

FEATURES

- Complementary To KTA1505.
- Excellent H_{FE} Linearity.
- Low noise.
- NPN Silicon Epitaxial Planar Transistor
- General purpose application, switching application.

MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	35	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	500	mA
P_C	Collector Power Dissipation	150	mW
T_j,T_{stg}	Junction and Storage Temperature	-55 to +150	℃

PACKAGE INFORMATION

Device	Package	Shipping
KTC3876	SOT-23	3000/Tape&Reel

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=100μA,I_E=0	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA,I_B=0	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA,I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=35V,I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V,I_C=0			0.1	μA
DC current gain	h_{FE}	V_{CE}=1V,I_C=100mA V_{CE}=6V,I_C=400mA	70 25		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=100mA, I_B=10mA		0.1	0.25	V
Base-emitter voltage	V_{BE}	V_{CE}=1V,I_C=100mA		0.8	1.0	V
Transition frequency	f_T	V_{CE}=6V, I_C= 20mA		300		MHz
Collector output capacitance	C_{ob}	V_{CB}=6V,I_E=0,f=1MHz		7		pF

CLASSIFICATION OF h_{FE}

Rank	O	Y	G
Range	70-140	120-240	200-400
Marking	WO	WY	WG